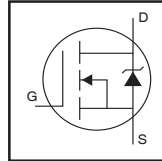


# AUIRFR4292 AUIRFU4292

## Features

- Advanced Process Technology
- Low On-Resistance
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to  $T_{jmax}$
- Lead-Free, RoHS Compliant
- Automotive Qualified \*

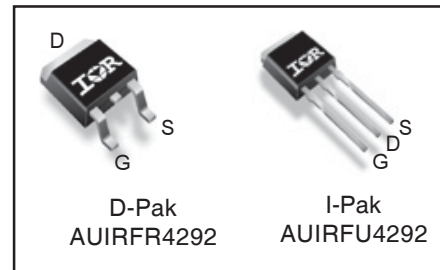


## HEXFET® Power MOSFET

$V_{(BR)DSS}$	<b>250V</b>
$R_{DS(on)}$ <b>typ.</b>	<b>275mΩ</b>
<b>max.</b>	<b>345mΩ</b>
$I_D$	<b>9.3A</b>

## Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.



<b>G</b>	<b>D</b>	<b>S</b>
Gate	Drain	Source

## Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature ( $T_A$ ) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	9.3	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	6.6	
$I_{DM}$	Pulsed Drain Current ①	40	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	100	W
	Linear Derating Factor	0.67	W/°C
$V_{GS}$	Gate-to-Source Voltage	± 20	V
$E_{AS}$	Single Pulse Avalanche Energy (Thermally Limited) ②	130	mJ
$E_{AS} (tested)$	Single Pulse Avalanche Energy Tested Value ③	97	
$I_{AR}$	Avalanche Current ④	See Fig.12a, 12b, 15, 16	A
$E_{AR}$	Repetitive Avalanche Energy ⑤		mJ
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)		

## Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑥	—	1.5	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ⑦	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

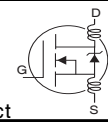
HEXFET® is a registered trademark of International Rectifier.

\*Qualification standards can be found at <http://www.irf.com/>

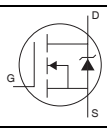
### Static Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	250	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.31	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1.0\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	275	345	m $\Omega$	$V_{GS} = 10V, I_D = 5.6A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.0	V	$V_{DS} = V_{GS}, I_D = 50\mu A$
$g_{fs}$	Forward Transconductance	6.2	—	—	V	$V_{DS} = 50V, I_D = 5.6A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	20	$\mu A$	$V_{DS} = 250V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 250V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$

### Dynamic Electrical @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge	—	13	20	nC	$I_D = 5.6A$
$Q_{gs}$	Gate-to-Source Charge	—	4.7	—		$V_{DS} = 125V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	4.8	—		$V_{GS} = 10V$ ③
$t_{d(on)}$	Turn-On Delay Time	—	11	—	ns	$V_{DD} = 250V$
$t_r$	Rise Time	—	15	—		$I_D = 5.6A$
$t_{d(off)}$	Turn-Off Delay Time	—	16	—		$R_G = 15\Omega$
$t_f$	Fall Time	—	8.4	—		$V_{GS} = 10V$ ③
$L_D$	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
$L_S$	Internal Source Inductance	—	7.5	—		
$C_{iss}$	Input Capacitance	—	705	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	71	—		$V_{DS} = 25V$
$C_{riss}$	Reverse Transfer Capacitance	—	20	—		$f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	600	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	26	—		$V_{GS} = 0V, V_{DS} = 200V, f = 1.0\text{MHz}$
$C_{oss\ eff.}$	Effective Output Capacitance	—	65	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 200V$ ④

### Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	9.3	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	40		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 5.6A, V_{GS} = 0V$ ③
$t_{rr}$	Reverse Recovery Time	—	110	165	ns	$T_J = 25^\circ\text{C}, I_F = 5.6A, V_{DD} = 125V$
$Q_{rr}$	Reverse Recovery Charge	—	390	585	nC	$di/dt = 100A/\mu s$ ③
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$ )				

#### Notes:

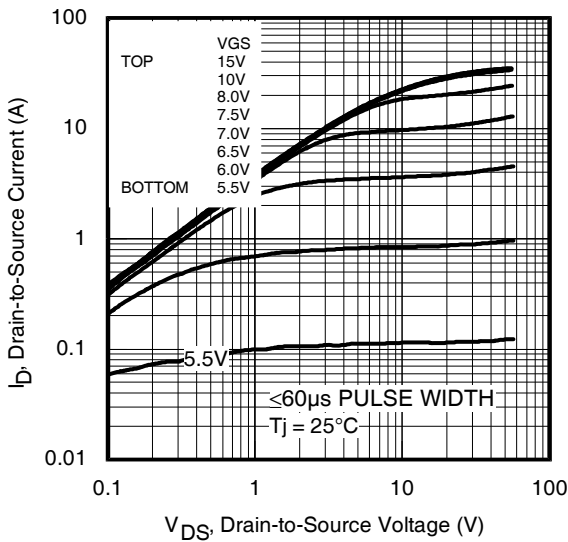
- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).
- ② Limited by  $T_{Jmax}$ , starting  $T_J = 25^\circ\text{C}, L = 8.1\text{mH}$   
 $R_G = 50\Omega, I_{AS} = 5.6A, V_{GS} = 10V$ . Part not recommended for use above this value.
- ③ Pulse width  $\leq 1.0\text{ms}$ ; duty cycle  $\leq 2\%$ .
- ④  $C_{oss\ eff.}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑤ Limited by  $T_{Jmax}$ , see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance.
- ⑥ This value is determined from sample failure population, starting  $T_J = 25^\circ\text{C}, L = 8.1\text{mH}$ ,  
 $R_G = 50\Omega, I_{AS} = 5.6A, V_{GS} = 10V$ .
- ⑦ When mounted on 1" square PCB (FR-4 or G-10 Material).  
For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑧  $R_G$  is measured at  $T_J$  approximately  $90^\circ\text{C}$ .

## Qualification Information<sup>†</sup>

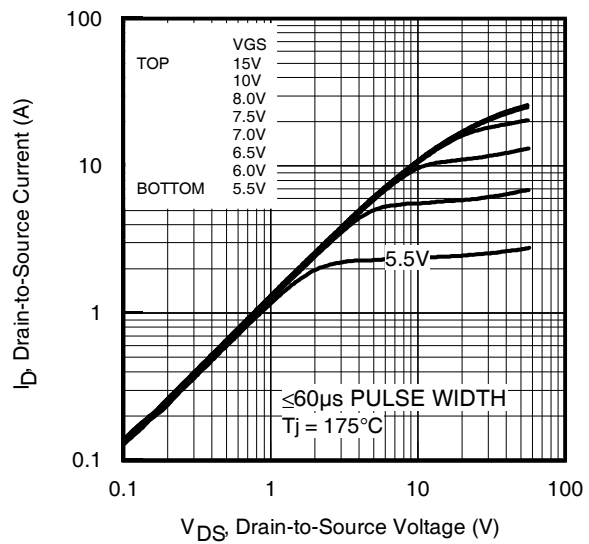
<b>Qualification Level</b>		Automotive (per AEC-Q101)	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
<b>Moisture Sensitivity Level</b>		D-PAK	MSL1
		I-PAK	N/A
<b>ESD</b>	Machine Model	Class M1B (+/- 100V) <sup>††</sup> AEC-Q101-002	
	Human Body Model	Class H1A (+/- 500V) <sup>††</sup> AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 2000V) <sup>††</sup> AEC-Q101-005	
<b>RoHS Compliant</b>		Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

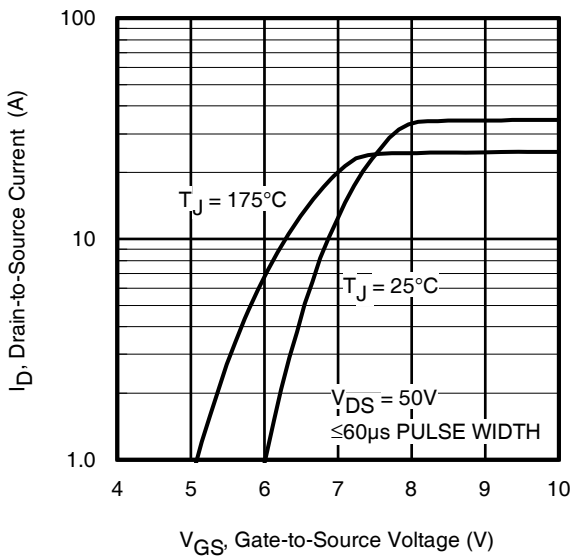
†† Highest passing voltage.



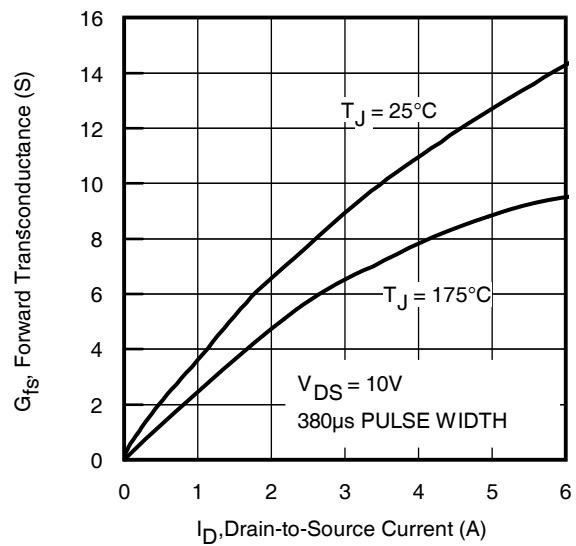
**Fig 1.** Typical Output Characteristics



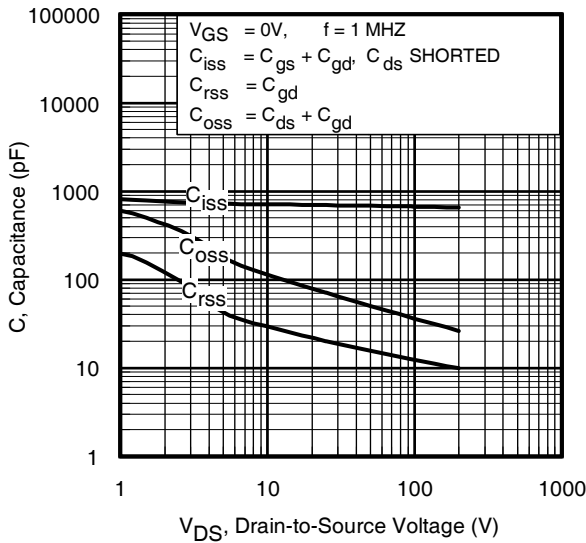
**Fig 2.** Typical Output Characteristics



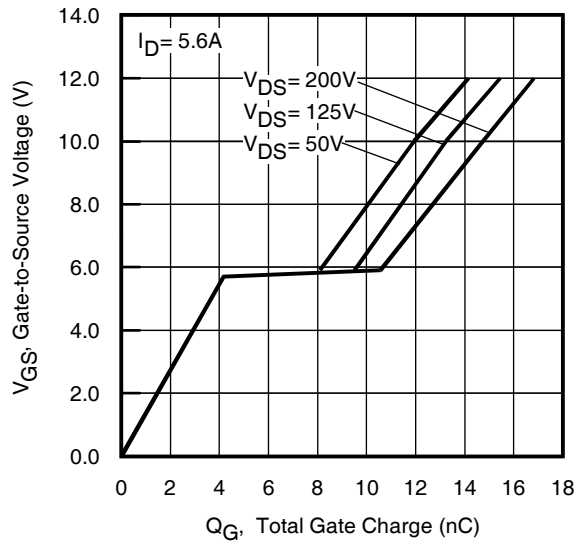
**Fig 3.** Typical Transfer Characteristics



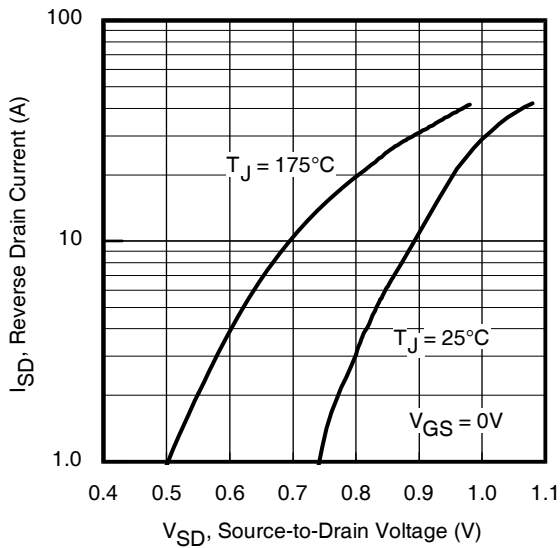
**Fig 4.** Typical Forward Transconductance vs. Drain Current



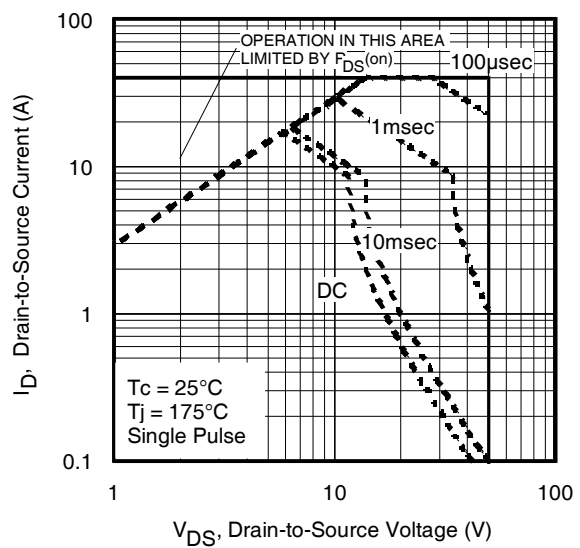
**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage



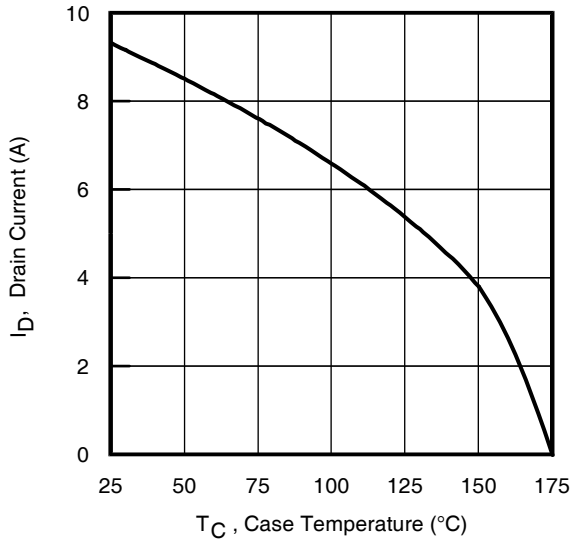
**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage



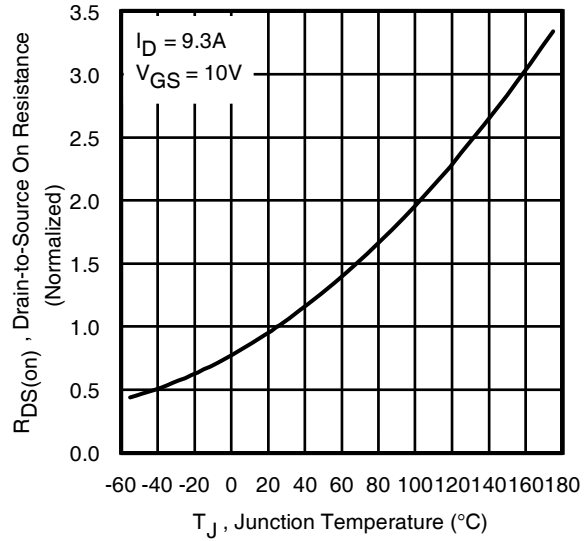
**Fig 7.** Typical Source-Drain Diode Forward Voltage



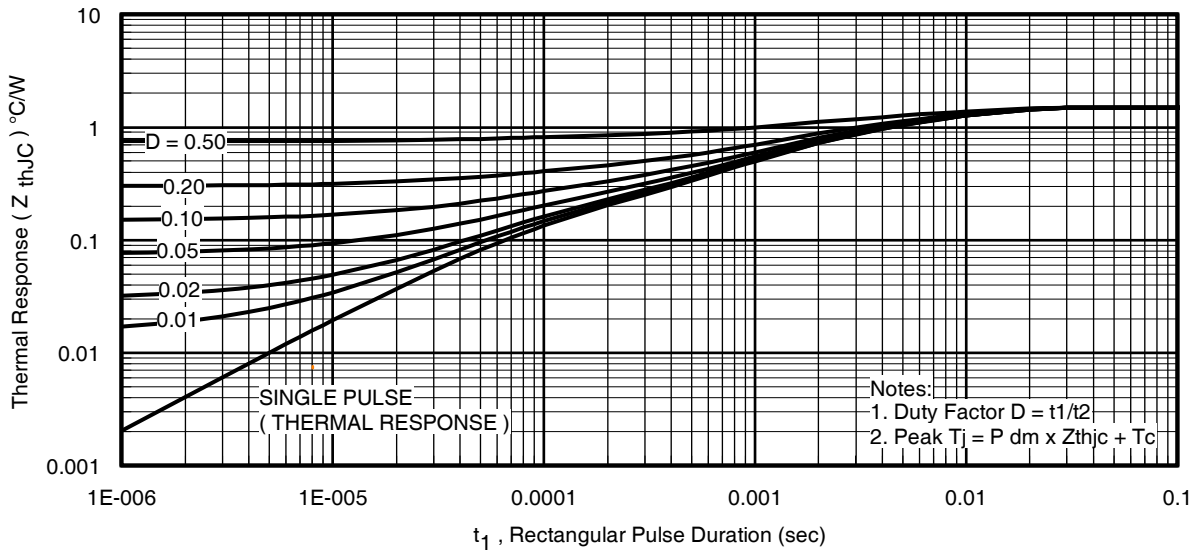
**Fig 8.** Maximum Safe Operating Area



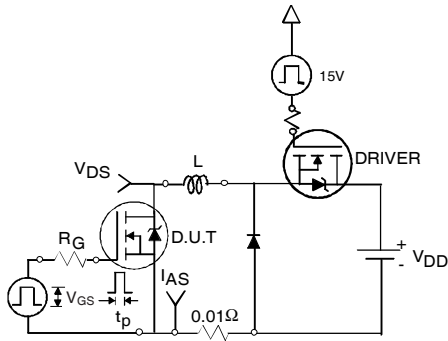
**Fig 9.** Maximum Drain Current vs. Case Temperature



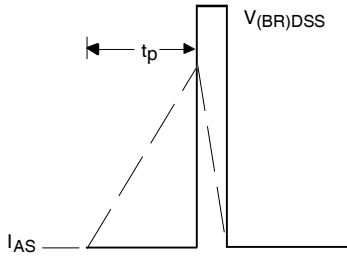
**Fig 10.** Normalized On-Resistance vs. Temperature



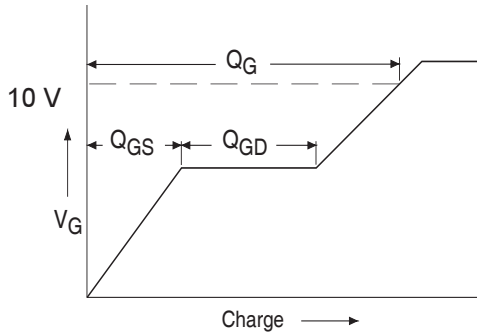
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



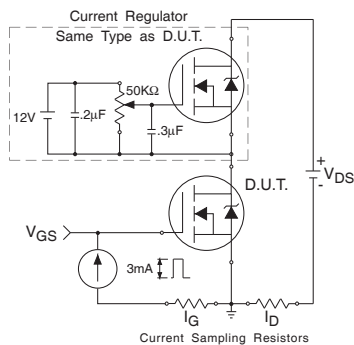
**Fig 12a.** Unclamped Inductive Test Circuit



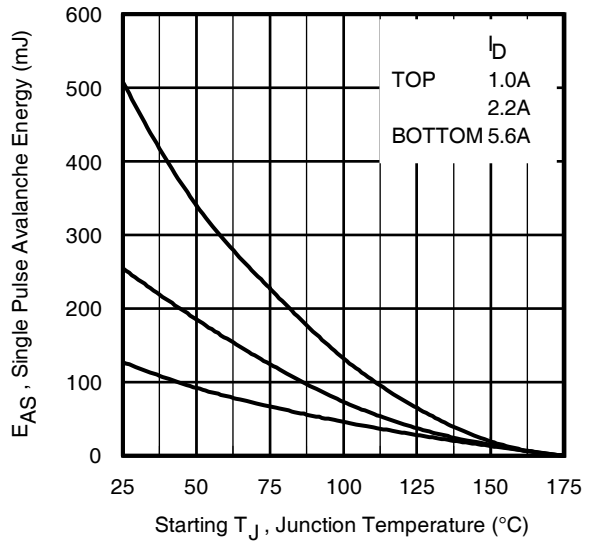
**Fig 12b.** Unclamped Inductive Waveforms



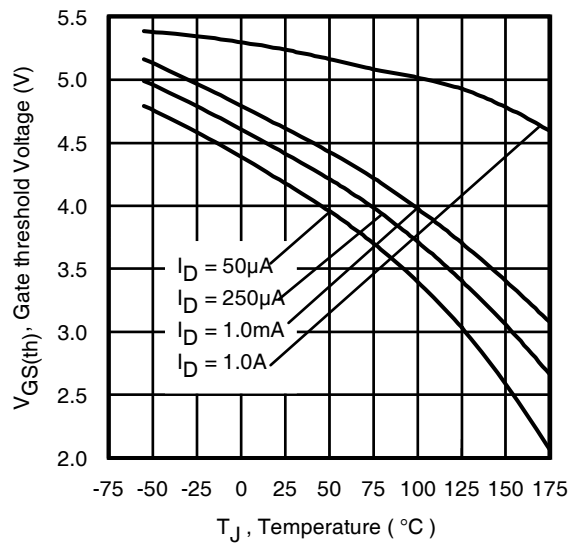
**Fig 13a.** Basic Gate Charge Waveform



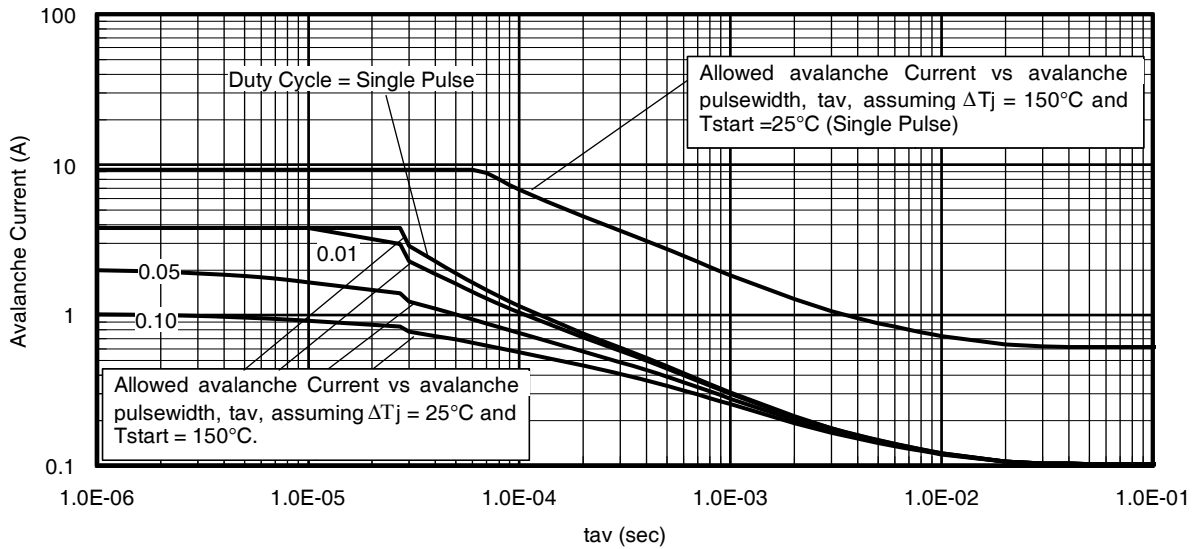
**Fig 13b.** Gate Charge Test Circuit



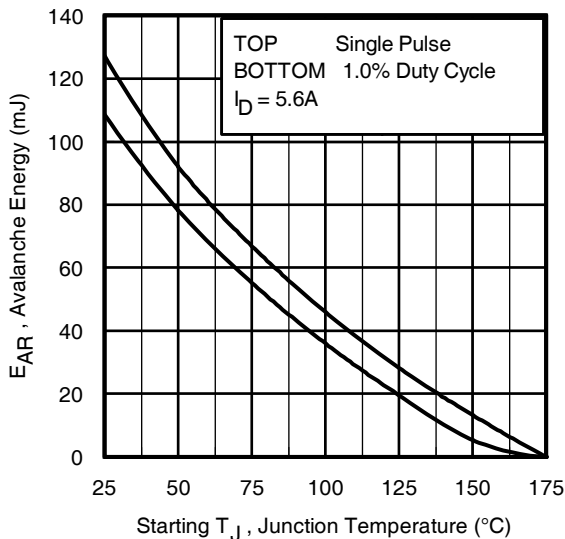
**Fig 12c.** Maximum Avalanche Energy vs. Drain Current



**Fig 14.** Threshold Voltage vs. Temperature



**Fig 15.** Typical Avalanche Current vs.Pulsewidth



**Fig 16.** Maximum Avalanche Energy vs. Temperature

**Notes on Repetitive Avalanche Curves , Figures 15, 16:**  
(For further info, see AN-1005 at [www.irf.com](http://www.irf.com))

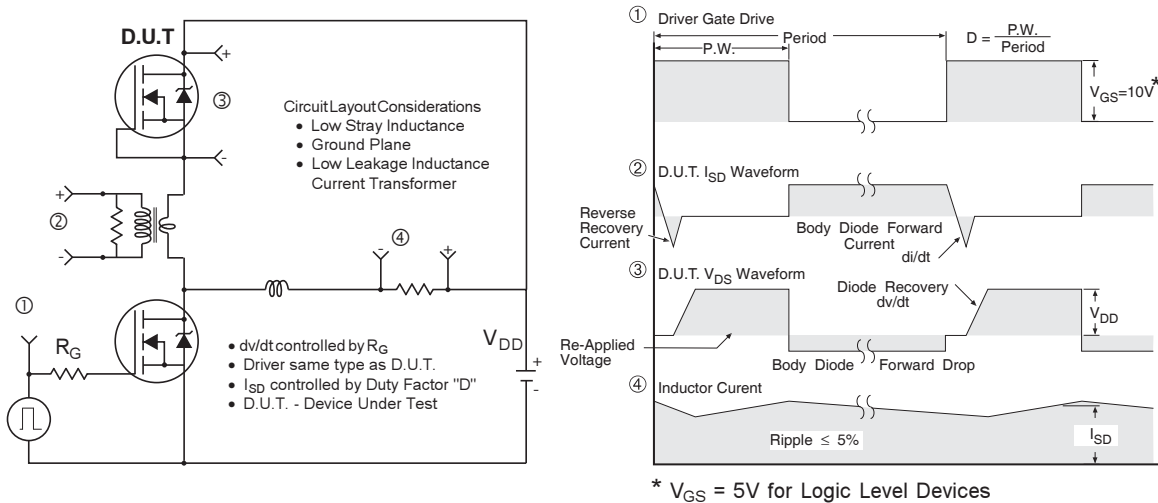
1. Avalanche failures assumption:  
Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed  $T_{jmax}$  (assumed as 25°C in Figure 15, 16).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see figure 11)

$$P_{D(ave)} = 1/2 ( 1.3 \cdot BV \cdot I_{av} ) = \Delta T / Z_{thJC}$$

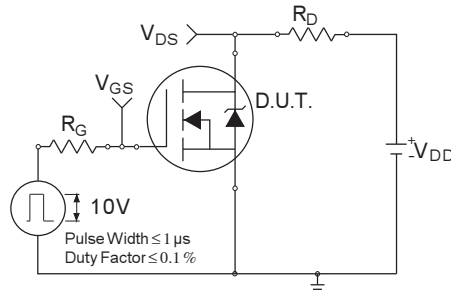
$$I_{av} = 2 \Delta T / [ 1.3 \cdot BV \cdot Z_{th} ]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

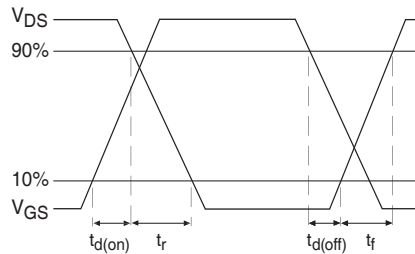




**Fig 17. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs**



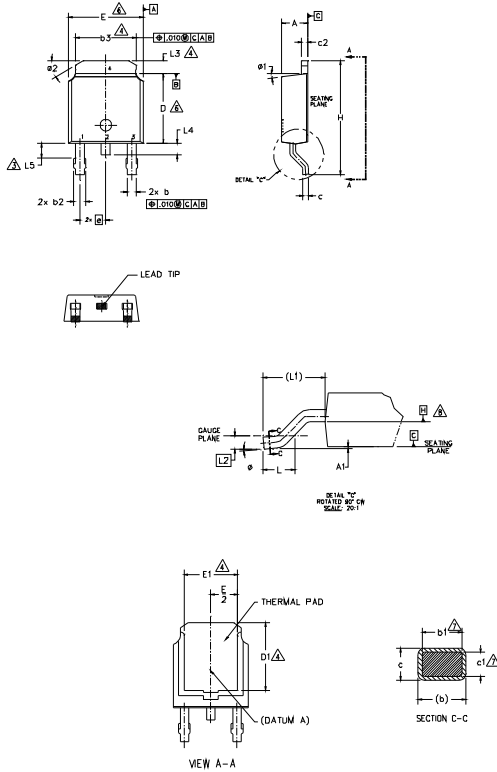
**Fig 18a. Switching Time Test Circuit**



**Fig 18b. Switching Time Waveforms**

## D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
  - 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
  - 3.- LEAD DIMENSION UNCONTROLLED IN L.S.
  - 4.- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
  - 5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
  - 6.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
  - 7.- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
  - 8.- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
  - 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	7
A1	-	0.13	-	.005	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	
D1	5.21	-	.205	-	
E	6.35	6.73	.250	.265	
E1	4.32	-	.170	-	
e	2.29 BSC		.090 BSC		
H	9.40	10.41	.370	.410	6
L	1.40	1.78	.055	.070	
L1	2.74 BSC		.108 REF.		
L2	0.51 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	4
L4	-	1.02	-	.040	
L5	1.14	1.52	.045	.060	
ø	0"	10"	0"	10"	
ø1	0"	15"	0"	15"	
ø2	25"	35"	25"	35"	3

**LEAD ASSIGNMENTS**

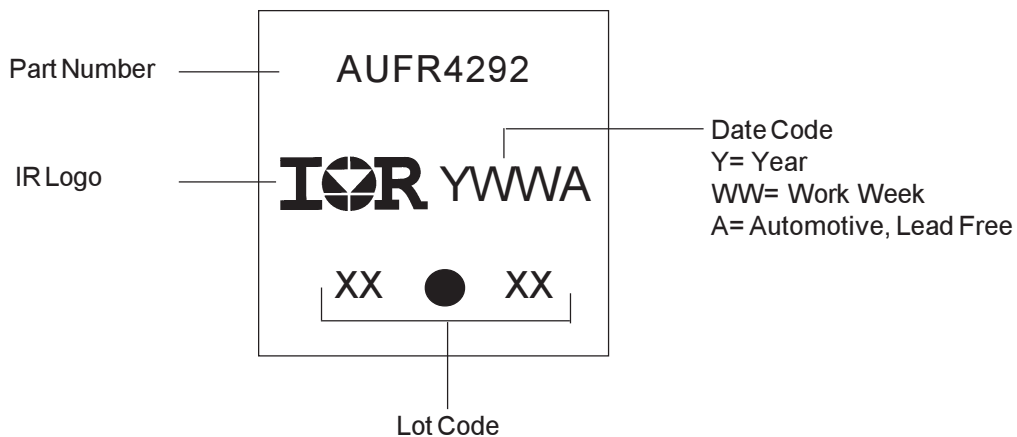
**HEXFET**

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

**IGBT & C<sub>g</sub>PAK**

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

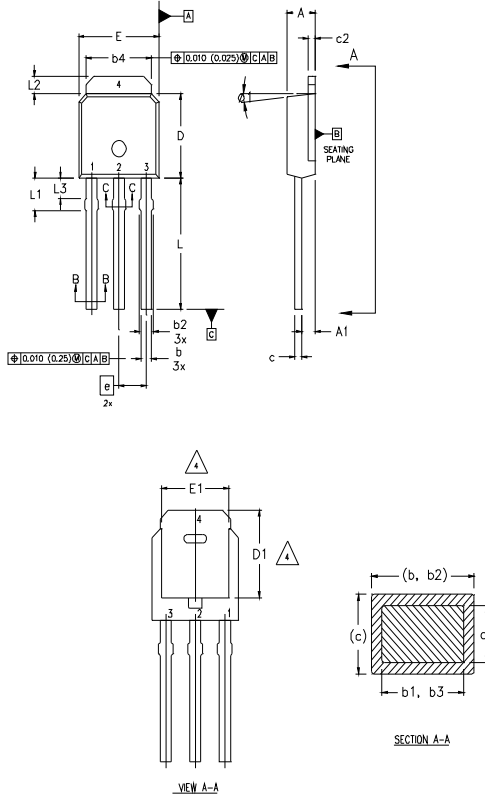
## D-Pak (TO-252AA) Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

## I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



**NOTES:**

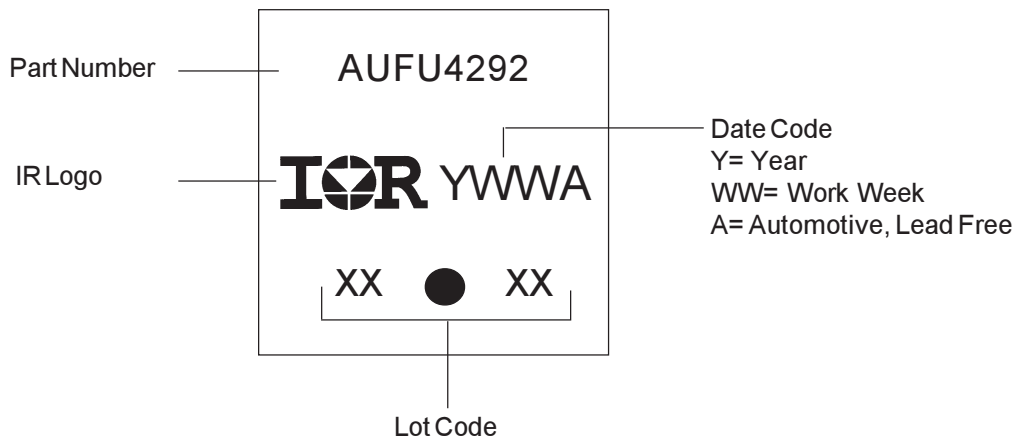
- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 4 THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
- 5 LEAD DIMENSION UNCONTROLLED IN L3.
- 6 DIMENSION b1, b3 APPLY TO BASE METAL ONLY.
- 7 OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA.
- 8 CONTROLLING DIMENSION : INCHES.

**LEAD ASSIGNMENTS**

- HEXFET**
- 1.- GATE
  - 2.- DRAIN
  - 3.- SOURCE
  - 4.- DRAIN

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	0.086	.094	
A1	0.89	1.14	0.035	0.045	
b	0.64	0.89	0.025	0.035	
b1	0.64	0.79	0.025	0.031	4
b2	0.76	1.14	0.030	0.045	
b3	0.76	1.04	0.030	0.041	
b4	5.00	5.46	0.195	0.215	4
c	0.46	0.61	0.018	0.024	
c1	0.41	0.56	0.016	0.022	
c2	.046	0.86	0.018	0.035	
D	5.97	6.22	0.235	0.245	3, 4
D1	5.21	-	0.205	-	4
E	6.35	6.73	0.250	0.265	3, 4
E1	4.32	-	0.170	-	4
e	2.29		0.090 BSC		
L	8.89	9.60	0.350	0.380	
L1	1.91	2.29	0.075	0.090	
L2	0.89	1.27	0.035	0.050	4
L3	1.14	1.52	0.045	0.060	5
ø1	0	15	0	15	

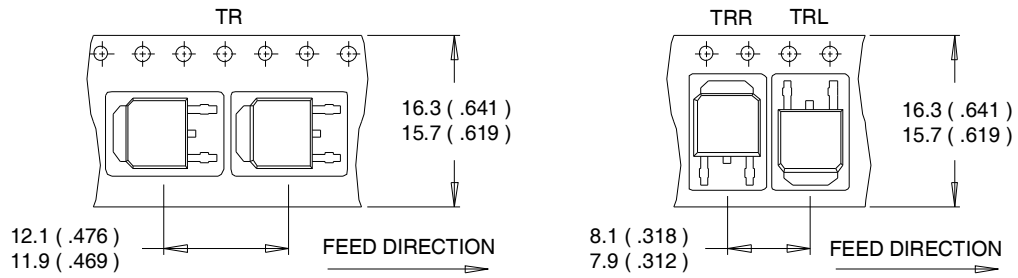
## I-Pak (TO-251AA) Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

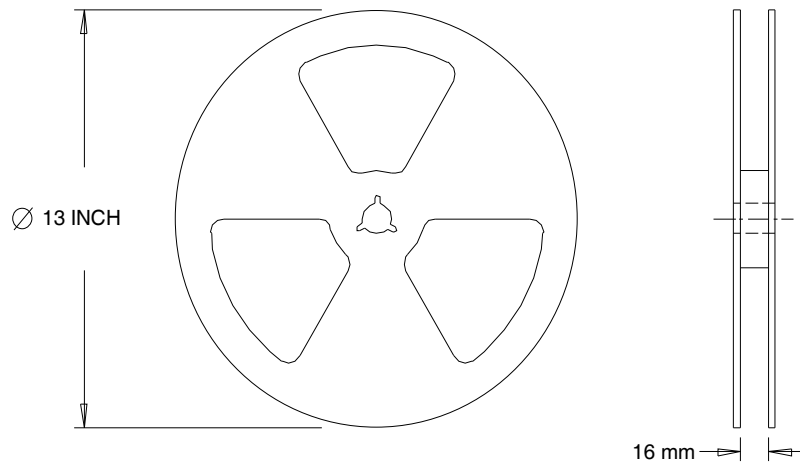
## D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



**NOTES :**

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



**NOTES :**

1. OUTLINE CONFORMS TO EIA-481.

## Ordering Information

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRFR4292	DPak	Tube	75	AUIRFR4292
		Tape and Reel	2000	AUIRFR4292TR
		Tape and Reel Left	3000	AUIRFR4292TRL
		Tape and Reel Right	3000	AUIRFR4292TRR
AUIRFU4292	IPak	Tube	75	AUIRFU4292

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